

VERSION SHOWING CHANGES BEING MADE

IN THE CLAIMS

Please amend the claims as follows:

2. (Three Times Amended) The [film acoustic wave device] wafer according to claim [1] 42, wherein a length of the at least one upper electrode is dependent upon the position at which the film acoustic wave device is mounted on the wafer.

3. (Three Times Amended) The [film acoustic wave device] wafer according to claim [1] 42, wherein a width of the upper electrode is dependent upon the position at which the film acoustic wave device is mounted on the wafer.

4. (Three Times Amended) The [film acoustic wave device] wafer according to claim [1] 42 further including a plurality of upper electrodes, wherein

distances between each of the plurality of upper electrodes are dependent upon the position at which the film acoustic wave device is mounted on the wafer.

5. (Three Times Amended) The [film acoustic wave device] wafer according to claim [1] 42 further comprising:

a bonding pad for connecting with the at least one upper electrode, wherein

the pattern shape of the film acoustic wave device is formed by at least the ground electrode, the piezoelectric thin film, the at least one upper electrode, and the bonding pad, and wherein

a shape of the bonding pad is dependent upon the position at which the film acoustic wave device is mounted on the wafer.

6. (Three Times Amended) The [film acoustic wave device] wafer according to claim 5 further comprising:

a connecting pattern for connecting the upper electrode with the bonding pad, wherein

the pattern shape of the film acoustic wave device is formed by at least the ground electrode, the piezoelectric thin film, the at least one upper electrode, the bonding pad, and the connecting pattern, and wherein

a shape of the connecting pattern is dependent upon the position at which the film acoustic wave device is mounted on the wafer.

7. The [film acoustic wave device] wafer according to claim 6, wherein the connecting pattern forms an air bridge.

8. (Three Times Amended) The [film acoustic wave device] wafer according to claim [1] 42 further comprising:

a capacitor provided on the same wafer as the film acoustic wave device, wherein

a capacitance of the capacitor is dependent upon the position at which the film acoustic wave device is mounted on the wafer.

9. (Twice Amended) The [film acoustic wave device] wafer according to claim [1] 42, wherein the wafer is made of gallium arsenide (GaAs), the piezoelectric thin film is made of lead titanate (PbTiO₃), and at least one upper electrode is a conductor substantially made of platinum (Pt).

10. (Twice Amended) The [film acoustic wave device] wafer according to claim [1] 42, wherein the wafer is made of silicon (Si), the piezoelectric thin film is made of lead titanate (PbTiO₃), and at least one upper electrode is a conductor substantially made of platinum (Pt).

11. (Twice Amended) The [film acoustic wave device] wafer according to claim [1] 42, wherein the piezoelectric thin film is made of PZT ($\text{PbTiO}_3\text{-PbZrO}_3$), and at least one upper electrode and the ground electrode is a conductor substantially made of platinum (Pt).

12. The [film acoustic wave device] wafer according to claim [1] 42, wherein the piezoelectric thin film is made of zinc oxide (ZnO).

13. (Amended) The [film acoustic wave device] wafer according to claim [1] 42, wherein the piezoelectric thin film is made of aluminum nitride (AlN).

14. (Twice Amended) The [film acoustic wave device] wafer according to claim [1] 42 further comprising:
an inductor positioned between the wafer and the ground electrode.

Claims 1, 15, 25 and 27-41 have been cancelled.

Claim 42-62 have been added.